



HAT2116H

Silicon N Channel Power MOS FET Power Switching

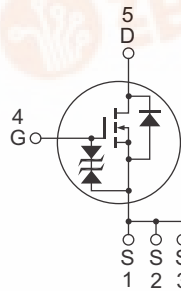
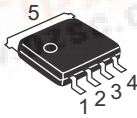
REJ03G1189-0400
(Previous: ADE-208-1575B)
Rev.4.00
Sep 07, 2005

Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 6.3 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)

Outline

RENESAS Package code: PTZZ0005DA-A
(Package name: LPAK)



1, 2, 3	Source
4	Gate
5	Drain



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	30	A
Drain peak current	I _{D (pulse)} ^{Note 1}	120	A
Body-drain diode reverse drain current	I _{DR}	30	A
Channel dissipation	P _{ch} ^{Note 2}	15	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. T_c = 25 °C

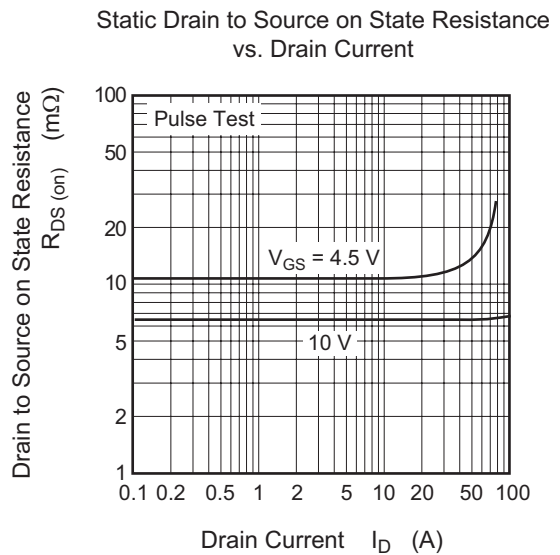
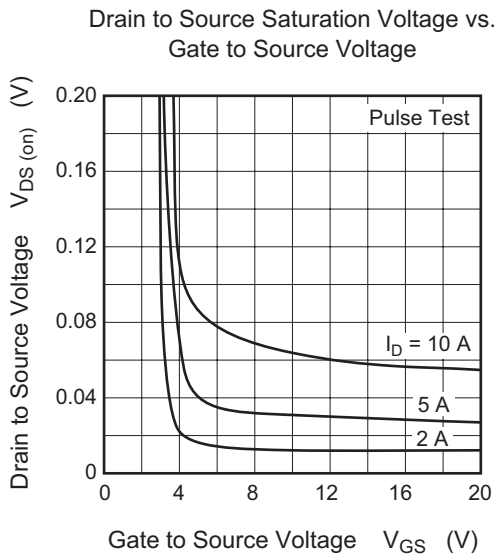
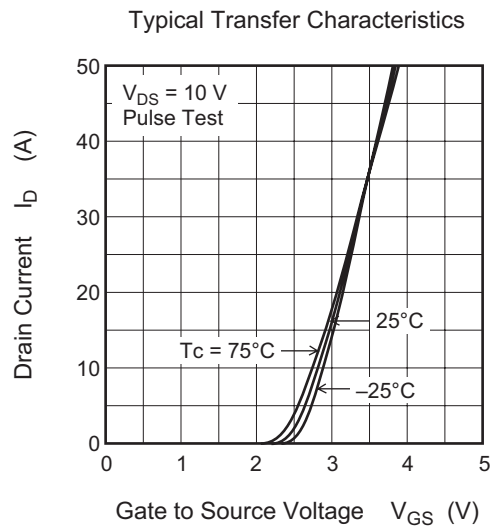
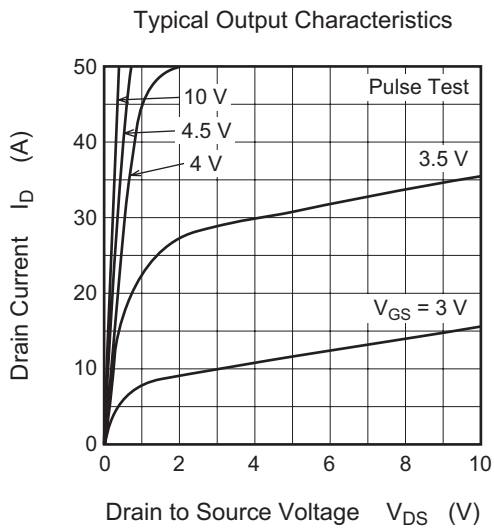
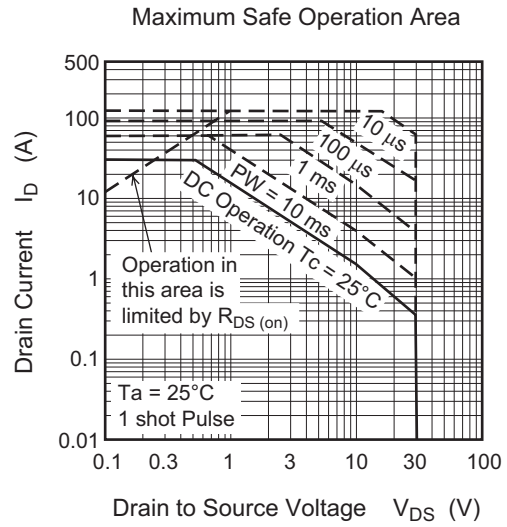
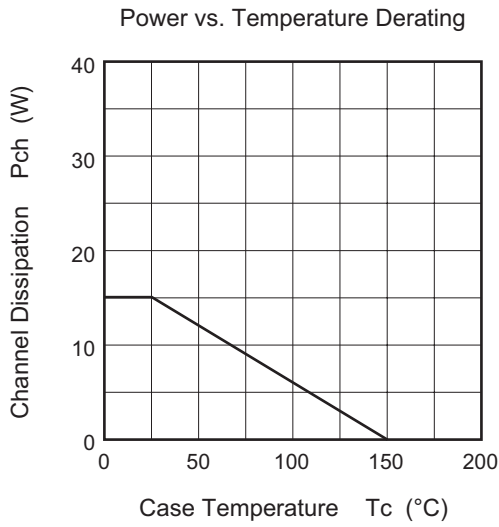
Electrical Characteristics

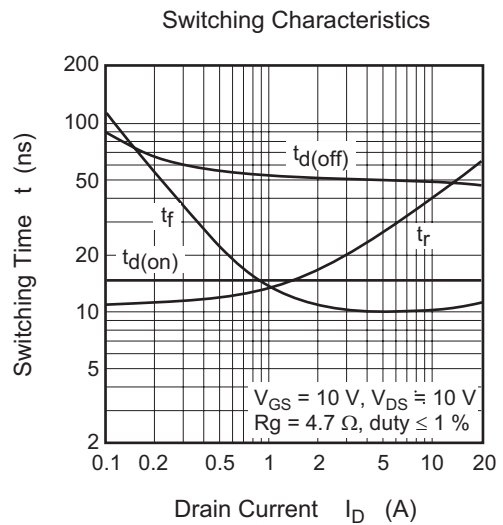
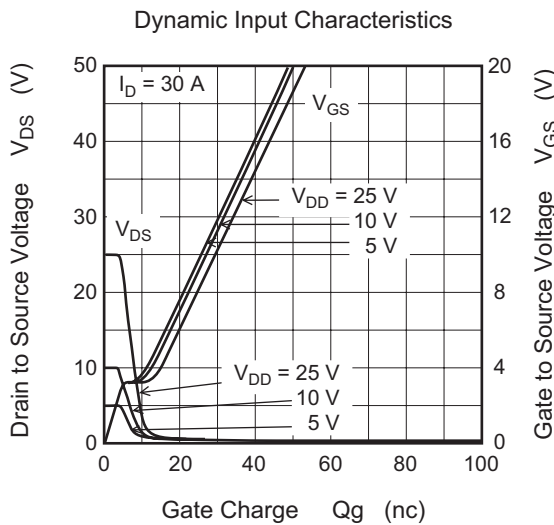
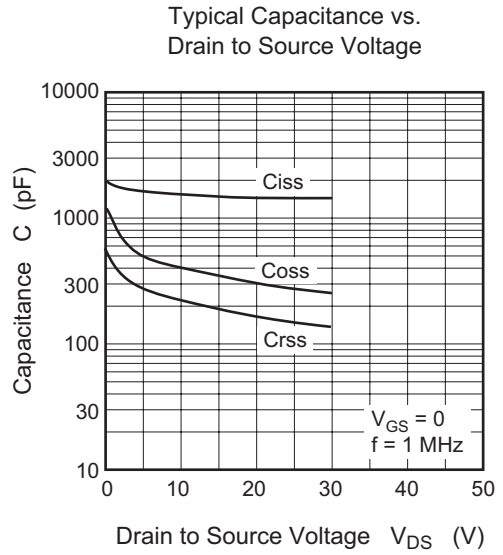
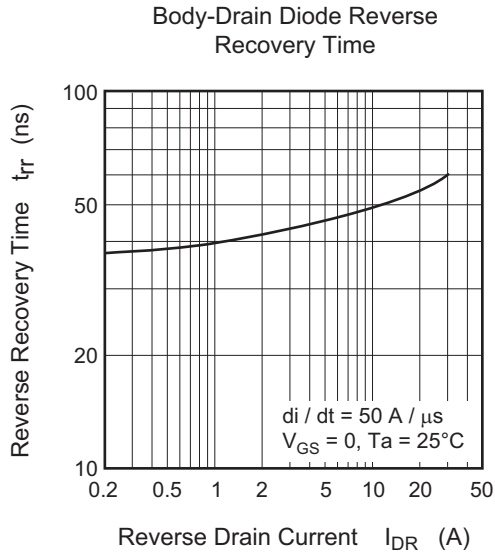
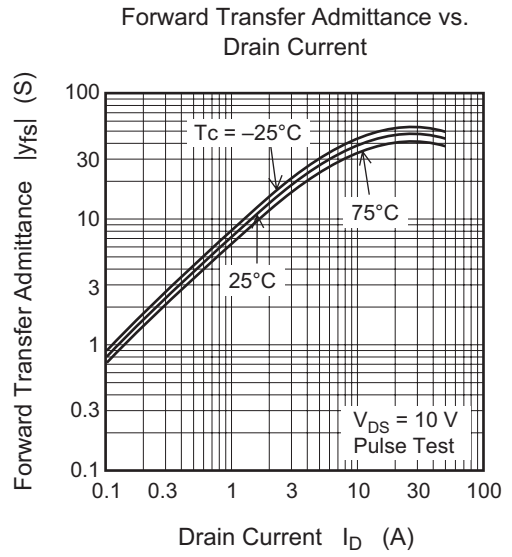
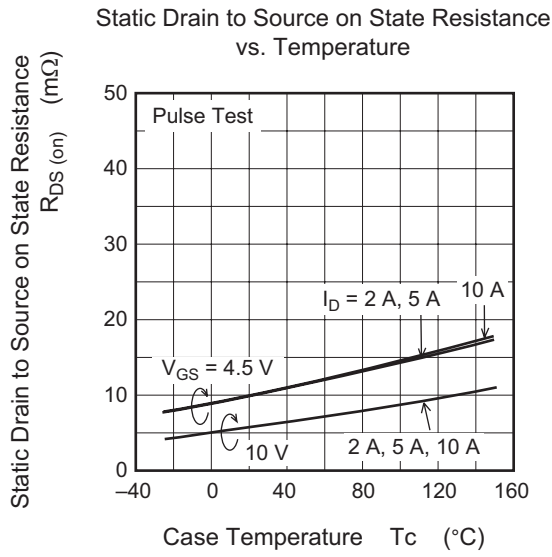
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	30	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 30 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	1.0	—	2.5	V	V _{DS} = 10 V, I _D = 1 mA
Static drain to source on state resistance	R _{DS (on)}	—	6.3	8.2	mΩ	I _D = 15 A, V _{GS} = 10 V ^{Note 3}
	R _{DS (on)}	—	10.5	15.3	mΩ	I _D = 15 A, V _{GS} = 4.5 V ^{Note 3}
Forward transfer admittance	y _{fs}	27	45	—	S	I _D = 15 A, V _{DS} = 10 V ^{Note 3}
Input capacitance	C _{iss}	—	1650	—	pF	V _{DS} = 10 V
Output capacitance	C _{oss}	—	400	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	220	—	pF	f = 1 MHz
Total gate charge	Q _g	—	26	—	nC	V _{DD} = 10 V
Gate to source charge	Q _{gs}	—	5	—	nC	V _{GS} = 10 V
Gate to drain charge	Q _{gd}	—	5	—	nC	I _D = 30 A
Turn-on delay time	t _{d (on)}	—	15	—	ns	V _{GS} = 10 V, I _D = 15 A
Rise time	t _r	—	55	—	ns	V _{DD} ≅ 10 V
Turn-off delay time	t _{d (off)}	—	48	—	ns	R _L = 0.5 Ω
Fall time	t _f	—	11	—	ns	R _g = 4.7 Ω
Body-drain diode forward voltage	V _{DF}	—	0.85	1.11	V	I _F = 30 A, V _{GS} = 0 ^{Note 3}
Body-drain diode reverse recovery time	t _{rr}	—	60	—	ns	I _F = 30 A, V _{GS} = 0 di _F /dt = 50 A/μs

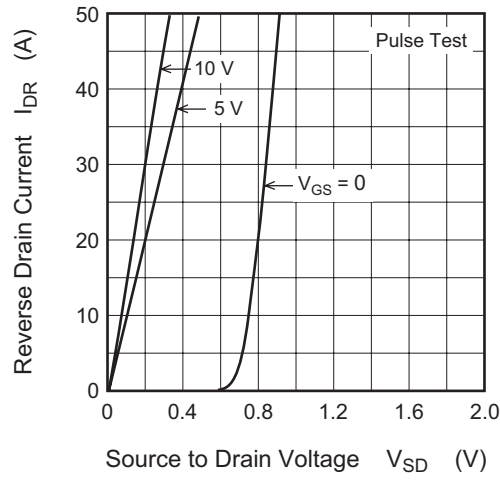
Note: 3. Pulse test

Main Characteristics

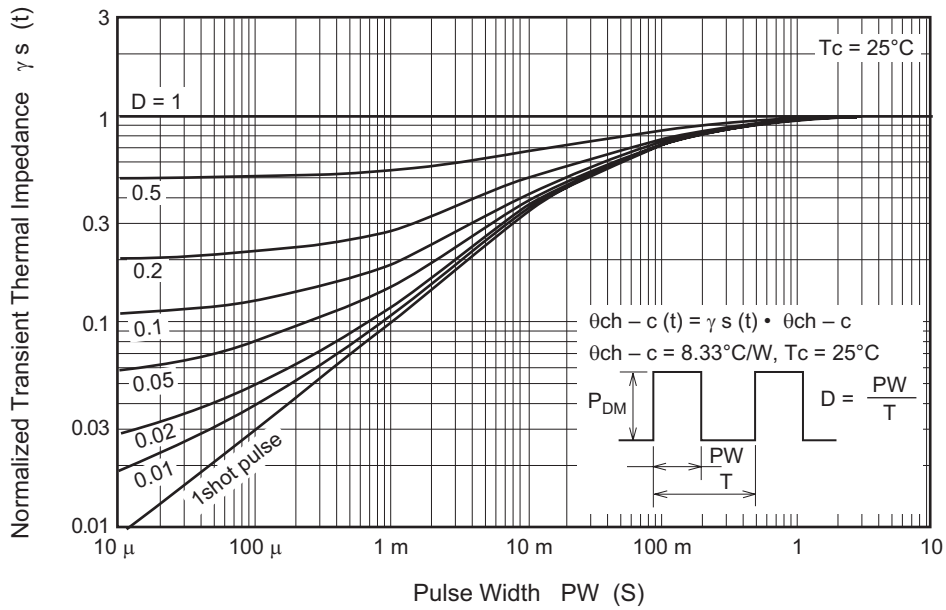




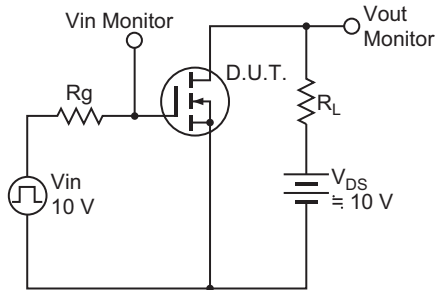
Reverse Drain Current vs. Source to Drain Voltage



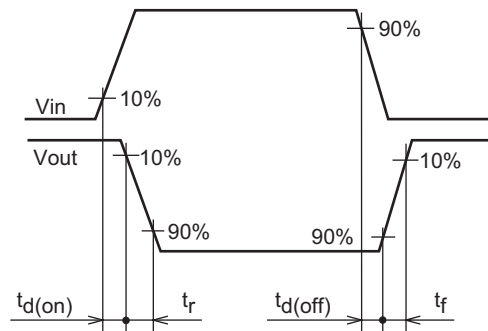
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit

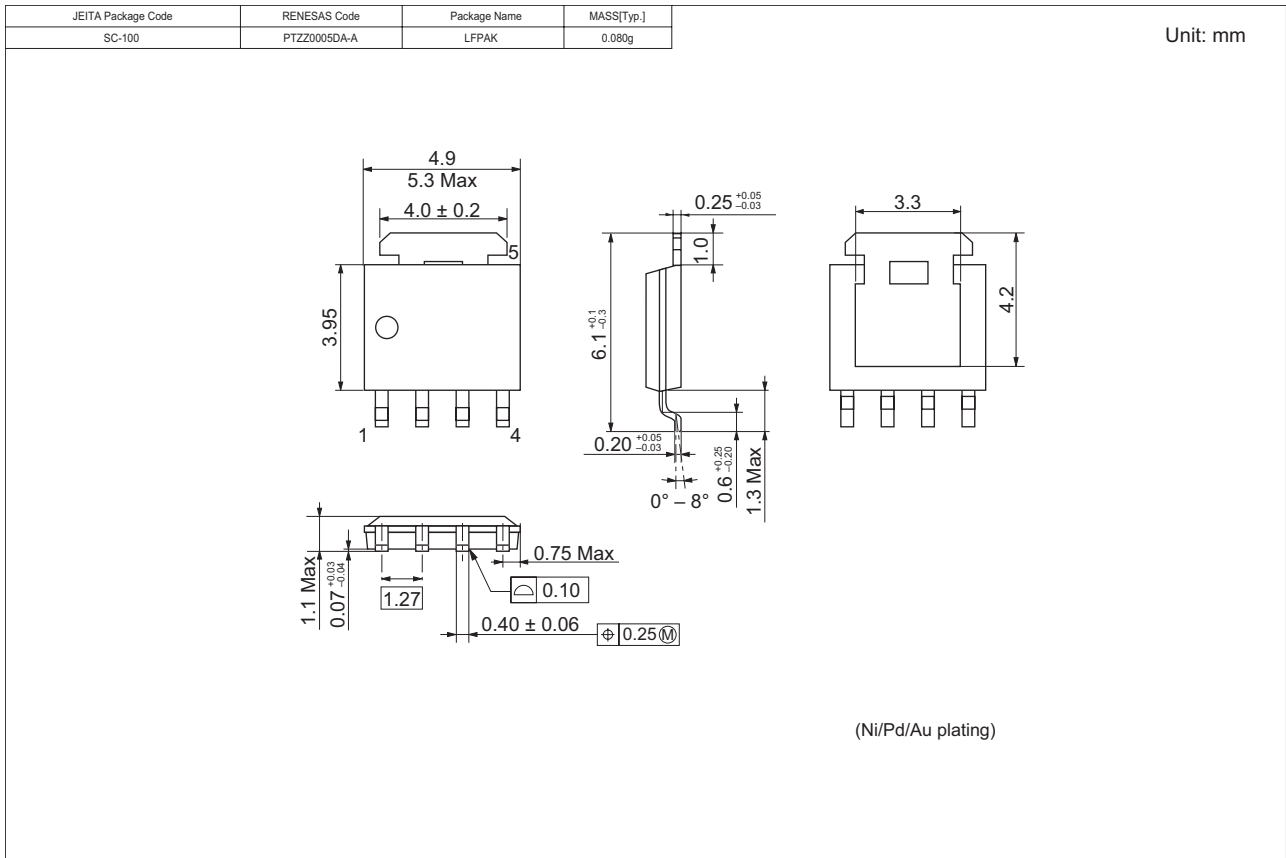


Switching Time Waveform



HAT2116H

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2116H-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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